# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

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### KL2G-1010-SiO2/Si

KL2G-1010-SiO2/Si is a single 10mmx10mm bilayer of CVD graphene film, on silicon. Both layers of graphene were grown on copper foil, and transferred individually by wet film transfer to the silicon substrate.

#### **Graphene Film**

Growth Method	CVD synthesis
Transfer Method	Clean transfer method
Quality Control	Optical Microscopy & Raman checked
Appearance (Color)	Transparent
Transparency	>97%
Appearance (Form)	Film
Coverage	>95%
Number of graphene layers	2
Thickness (theoretical)	0.345 nm
Field Effect Mobility on SiO <sub>2</sub> /Si	2,000 cm <sup>2</sup> /V·s
Hall Effect Mobility on SiO <sub>2</sub> /Si	4,000 cm <sup>2</sup> /V·s
Sheet Resistance on SiO <sub>2</sub> /Si (Van der Pauw)	190±30 Ohms/sq. (1cm x 1cm)
Grain size	Up to 10 µm





#### Substrate

	SiO <sub>2</sub> /Si
Type/Dopant	P/Bor
Orientation	<100>
Growth Method	CZ
Resistivity	<0.005 ohm cm
Thickness	525 +/- 20 μm
Front Surface	Polished
Back Surface	Etched
Flats	2 SEMI

#### **Optical Microscopy**



